

In the Claims:

4 (currently amended). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than 50 μ m;

activating all of the first insulating layer by treatment with an activator;

then applying and patterning a second insulating layer made of a photosensitive material; and

then seeding and metallizing regions of the first insulating layer that are exposed by the patterning step.

5 (original). The process according to claim 4, which comprises forming the first insulating layer and the second insulating layer from the same material.

6 (original). The process according to claim 5, which comprises patterning the first insulating layer before the second insulating layer is applied.

7 (original). The process according to claim 4, which comprises patterning the first insulating layer before the second insulating layer is applied.